

1GB – 2x64Mx64, SDRAM UNBUFFERED

FEATURES

- PC100 and PC133 compatible
- Burst Mode Operation
- Auto and Self Refresh capability
- LVTTL compatible inputs and outputs
- Serial Presence Detect with EEPROM
- Fully synchronous: All signals are registered on the positive edge of the system clock
- Programmable Burst Lengths: 1, 2, 4, 8 or Full Page
- 3.3V $\pm$ 0.3V Power Supply
- 168 Pin DIMM
 - PCB: 29.41mm (1.158")

DESCRIPTION

The WV3DG64127V is a 2x64Mx64 synchronous DRAM module which consists of sixteen stacked 64Mx8 bit with 4 banks SDRAM components in TSOP II package and one 2K EEPROM which are mounted on a 168 Pin DIMM multilayer FR4 Substrate.

* This product is under development, is not qualified or characterized and is subject to change or cancellation without notice.

NOTE: Consult factory for availability of:

- Lead-free products
- Vendor source control option
- Industrial temperature option

PIN CONFIGURATIONS (FRONT SIDE/BACK SIDE)

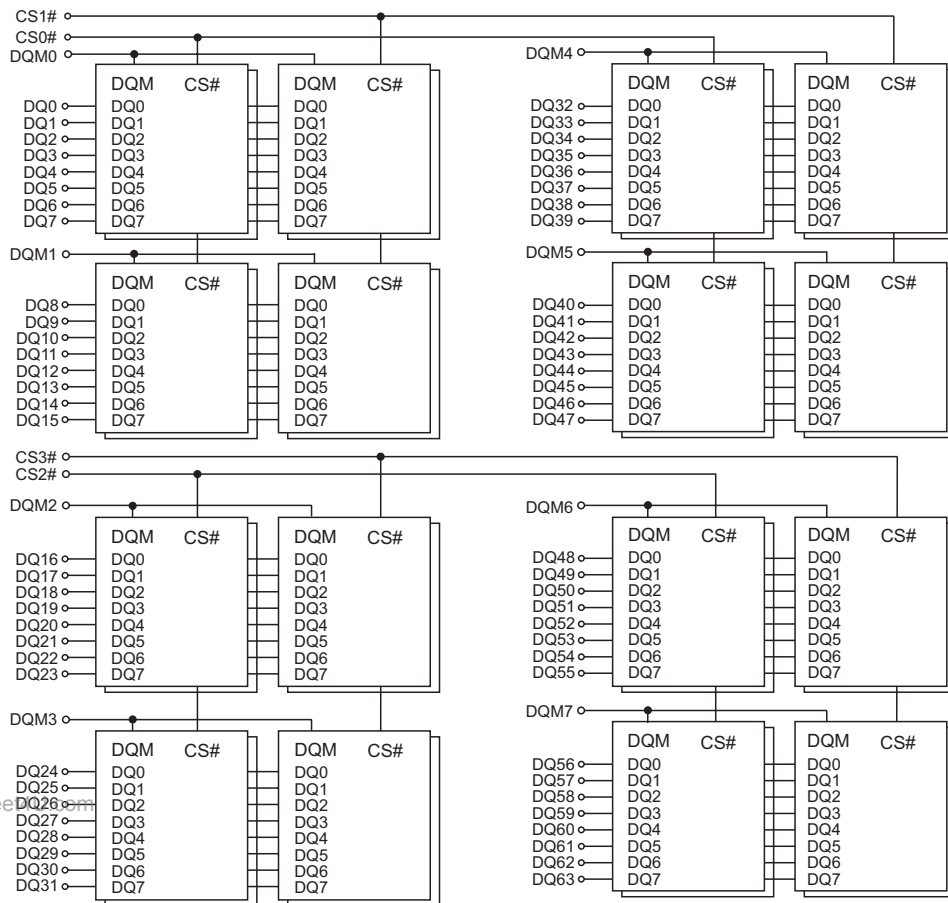
Pin	Front	Pin	Front	Pin	Front	Pin	Back	Pin	Back	Pin	Back
1	Vss	29	DQM1	57	DQ18	85	Vss	113	DQM5	141	DQ50
2	DQ0	30	CS0#	58	DQ19	86	DQ32	114	CS1#	142	DQ51
3	DQ1	31	DNU	59	Vcc	87	DQ33	115	RAS#	143	Vcc
4	DQ2	32	Vss	60	DQ20	88	DQ34	116	Vss	144	DQ52
5	DQ3	33	A0	61	NC	89	DQ35	117	A1	145	NC
6	Vcc	34	A2	62	NC	90	Vcc	118	A3	146	NC
7	DQ4	35	A4	63	CKE1	91	DQ36	119	A5	147	DNU
8	DQ5	36	A6	64	Vss	92	DQ37	120	A7	148	Vss
9	DQ6	37	A8	65	DQ21	93	DQ38	121	A9	149	DQ53
10	DQ7	38	A10/AP	66	DQ22	94	DQ39	122	BA0	150	DQ54
11	DQ8	39	BA1	67	DQ23	95	DQ40	123	A11	151	DQ55
12	Vss	40	Vcc	68	Vss	96	Vss	124	Vcc	152	Vss
13	DQ9	41	Vcc	69	DQ24	97	DQ41	125	CLK1	153	DQ56
14	DQ10	42	CLK0	70	DQ25	98	DQ42	126	A12	154	DQ57
15	DQ11	43	Vss	71	DQ26	99	DQ43	127	Vss	155	DQ58
16	DQ12	44	DNU	72	DQ27	100	DQ44	128	CKE0	156	DQ59
17	DQ13	45	CS2#	73	Vcc	101	DQ45	129	CS3#	157	Vcc
18	Vcc	46	DQM2	74	DQ28	102	Vcc	130	DQM6	158	DQ60
19	DQ14	47	DQM3	75	DQ29	103	DQ46	131	DQM7	159	DQ61
20	DQ15	48	DNU	76	DQ30	104	DQ47	132	NC	160	DQ62
21	CBO	49	Vcc	77	DQ31	105	CB4	133	Vcc	161	DQ63
22	CB1	50	NC	78	Vss	106	CB5	134	NC	162	Vss
23	Vss	51	NC	79	CLK2	107	Vss	135	NC	163	CLK3
24	NC	52	CB2	80	NC	108	NC	136	CB6	164	NC
25	NC	53	CB3	81	NC	109	NC	137	CB7	165	SA0
26	Vcc	54	Vss	82	SDA	110	Vcc	138	Vss	166	SA1
27	WE#	55	DQ16	83	SCL	111	CAS#	139	DQ48	167	SA2
28	DQM0	56	DQ17	84	Vcc	112	DQM4	140	DQ49	168	Vcc

PIN NAMES

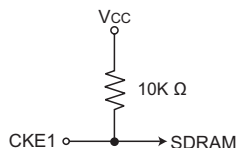
A0 – A12	Address input (Multiplexed)
BA0-1	Select Bank
DQ0-63	Data Input/Output
CLK0-CLK3	Clock input
CKE0, CKE1	Clock Enable input
CS0# - CS3#	Chip select Input
RAS#	Row Address Strobe
CAS#	Column Address Strobe
WE#	Write Enable
DQM0-7	DQM
Vcc	Power Supply
Vss	Ground
SDA	Serial data I/O
SCL	Serial clock
DNU	Do not use
NC	No Connect



FUNCTIONAL BLOCK DIAGRAM

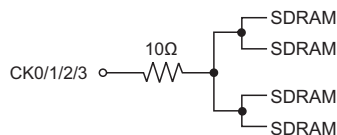
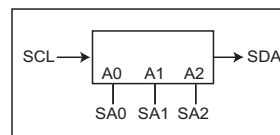


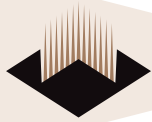
A0 ~ A12, BA0 & 1 → SDRAM
RAS# → SDRAM
CAS# → SDRAM
WE# → SDRAM
CKE0 → SDRAM



10Ω
DQn → Every DQpin of SDRAM

Vcc →
Vss →
Two 0.1μF Capacitors
per each SDRAM
To all SDRAMs





ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Units
Voltage on any pin relative to Vss	V _{IN} , V _{OUT}	-1.0 ~ 4.6	V
Voltage on Vcc supply relative to Vss	V _{CC} , V _{CCA}	-1.0 ~ 4.6	V
Storage Temperature	TSTG	-55 ~ +150	°C
Power Dissipation	PD	32	W
Short Circuit Current	IOS	50	mA

Note: Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded.
Functional operation should be restricted to recommended operating condition.
Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

RECOMMENDED DC OPERATING CONDITIONS

Voltage Referenced to: Vss = 0V, 0°C ≤ TA ≤ +70°C

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply Voltage	V _{CC}	3.0	3.3	3.6	V	
Input High Voltage	V _{IH}	2.0	3.0	V _{CCA} +0.3	V	1
Input Low Voltage	V _{IL}	-0.3	—	0.8	V	2
Output High Voltage	V _{OH}	2.4	—	—	V	I _{OH} = -2mA
Output Low Voltage	V _{OL}	—	—	0.4	V	I _{OL} = -2mA
Input Leakage Current	I _{LI}	-10	—	10	μA	3

Note:
1. V_{IH} (max)= 5.6V AC. The overshoot voltage duration is ≤ 3ns.
2. V_{IL} (min)= -2.0V AC. The undershoot voltage duration is ≤ 3ns.
3. Any input 0V ≤ V_{IN} ≤ V_{CC}
Input leakage currents include Hi-Z output leakage for all bi-directional buffers with Tri-State outputs.

CAPACITANCE

TA = 25°C, f = 1MHz, V_{CC} = 3.3V, V_{REF}=1.4V ± 200mV

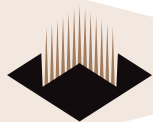
Parameter	Symbol	Max	Unit
Input Capacitance (A0-A12)	C _{IN1}	150	pF
Input Capacitance (RAS#,CAS#,WE#)	C _{IN2}	150	pF
Input Capacitance (CKE0-CKE1)	C _{IN3}	80	pF
Input Capacitance (CK0-CK3)	C _{IN4}	45	pF
Input Capacitance (CS0#-CS3#)	C _{IN5}	45	pF
Input Capacitance (DQM0-DQM7)	C _{IN6}	30	pF
Input Capacitance (BA0-BA1)	C _{IN7}	150	pF
Data input/output capacitance (DQ0-DQ63)	C _{OUT}	30	pF

**I_{DD} SPECIFICATIONS AND CONDITIONS**V_{CC}, V_{CCQ} = +3.3V ±0.3V; SDRAM component values only

Parameter	Symbol	Test Condition	Version			Unit	Note
			7	75	10		
Operating current (One bank active)	I _{CC1}	Burst length = 1, t _{RC} ≥ t _{RC} (min), IO = 0 mA	2080	1920	1920	mA	1
Precharge standby current in power-down mode	I _{CC2P}	CKE ≤ V _{IL} (max), t _{CC} = 10ns	64			mA	
	I _{CC2PS}	CKE & CLK ≥ V _{IL} (max), t _{CC} = ∞	64				
Precharge standby current in non power-down mode	I _{CC2N}	CKE ≥ V _{IH} (min), CS# ≥ V _{IH} (min), t _{CC} = 10ns Input signals are changed one time during 20ns	640			mA	
	I _{CC2NS}	CKE ≥ V _{IH} (min), CLK ≤ V _{IL} (max), t _{CC} = ∞ Input signals are stable	320				
Active standby current in power-down mode	I _{CC3P}	CKE ≤ V _{IL} (max), t _{CC} = 10ns	200			mA	
	I _{CC3PS}	CKE & CLK ≤ V _{IL} (max), t _{CC} = ∞	200				
Active standby current in non power-down mode (One bank active)	I _{CC3N}	CKE ≥ V _{IH} (min), CS# ≥ V _{IH} (min), t _{CC} = 10ns Input signals are changed one time during 20ns	960			mA	
	I _{CC3NS}	CKE ≥ V _{IH} (min), CLK ≤ V _{IL} (max), t _{CC} = ∞ Input signals are stable	800			mA	
Operating current (Burst mode)	I _{CC4}	IO = 0 mA Page burst 4banks Activated. t _{CCD} = 2CLKs	2240	2240	2080	mA	1
Refresh current	I _{CC5}	t _{RC} ≥ t _{RC} (min)	4000	3680	3520	mA	2
Self refresh current	I _{CC6}	CKE ≤ 0.2V	96			mA	

Notes:

1. Measured with outputs open.
2. Refresh period is 64ms.
3. Unless otherwise noted, input swing is CMOS (V_{IH}/V_{IL} = V_{CCQ}/V_{ISO})

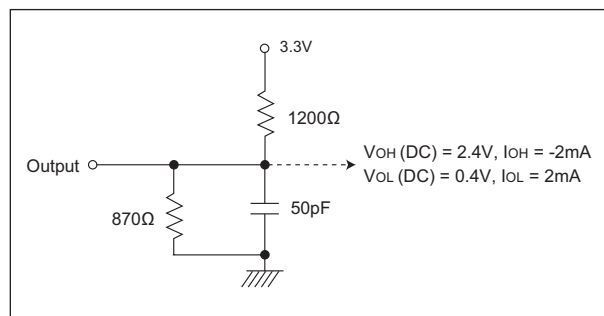


AC OPERATING TEST CONDITIONS

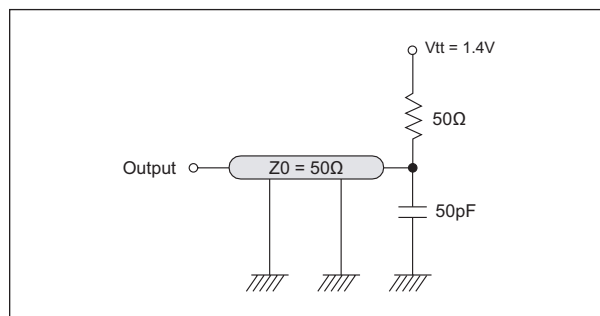
 $V_{CC}, V_{CCQ} = +3.3V \pm 0.3V, 0^{\circ}C - 70^{\circ}C$

Parameter	Value	Unit
AC input levels (V_{IH}/V_{IL})	2.4/0.4	V
Input timing measurement reference level	1.4	V
Input rise and fall time	$t_r/t_f = 1/1$	ns
Output timing measurement reference level	1.4	V
Output load condition	See Fig. 2	

DC OUTPUT LOAD CIRCUIT



AC OUTPUT LOAD CIRCUIT



OPERATING AC PARAMETER

 $V_{CC}, V_{CCQ} = +3.3V \pm 0.3V, 0^{\circ}C - 70^{\circ}C$

Parameter		Symbol	Version			Unit	Note
			7	75	10		
Row active to row active delay		tRRD(min)	15	15	20	ns	1
RAS# to CAS# delay		tRCD(min)	15	20	20	ns	1
Row precharge time		tRP(min)	15	20	20	ns	1
Row active time		tRAS(min)	45	45	50	ns	1
		tRAS(max)	100			us	
Row cycle time		tRC(min)	60	65	70	ns	1
Last data in to row precharge		tRDL(min)	2			CLK	2
Last data in to Active delay		tDAL(min)	2 CLK + tRP			—	
Last data in to new col. address delay		tCDL(min)	1			CLK	2
Last data in to burst stop		tBDL(min)	1			CLK	2
Col. address to col. address delay		tCCD(min)	1			CLK	3
Number of valid output data	CAS latency=3		2			ea	4
	CAS latency=2		1				

Notes:

- The minimum number of clock cycles is determined by dividing the minimum time required with clock cycle time and then rounding off to the next higher integer.
- Minimum delay is required to complete write.
- All parts allow every cycle column address change.
- In case of row precharge interrupt, auto precharge and read burst stop.



OPERATING AC PARAMETERS

$V_{CC}, V_{CCQ} = +3.3V \pm 0.3V, 0^{\circ}C - 70^{\circ}C$

Parameter		Symbol	7		75		10		Unit	Note
			Min	Max	Min	Max	Min	Max		
CLK cycle time	CAS latency=3	t_{CC}	7.5	1000	7.5	1000	10	1000	ns	1
	CAS latency=2		7.5		10		10			
CLK to valid output delay	CAS latency=3	t_{SAC}		5.4		5.4		6	ns	1, 2
	CAS latency=2			5.4		6		6		
Output data hold time	CAS latency=3	t_{OH}	3		3		3		ns	2
	CAS latency=2		3		3		3			
CLK high pulse width		t_{CH}	2.5		2.5		3		ns	3
CLK low pulse width		t_{CL}	2.5		2.5		3		ns	3
Input setup time		t_{SS}	1.5		1.5		2		ns	3
Input hold time		t_{SH}	0.8		0.8		1		ns	3
CLK to output in Low-Z		t_{SLZ}	1		1		1		ns	2
CLK to output in Hi-Z	CAS latency=3	t_{SHZ}		5.4		5.4		6	ns	
	CAS latency=2			5.4		6		6		

Notes :

- Parameters depend on programmed CAS latency.
- If clock rising time is longer than 1ns, $(t_r/2-0.5)ns$ should be added to the parameter.
- Assumed input rise and fall time (t_r & t_f) = 1ns.
If t_r & t_f is longer than 1ns, transient time compensation should be considered,
i.e., $[(t_r + t_f)/2-1]ns$ should be added to the parameter.



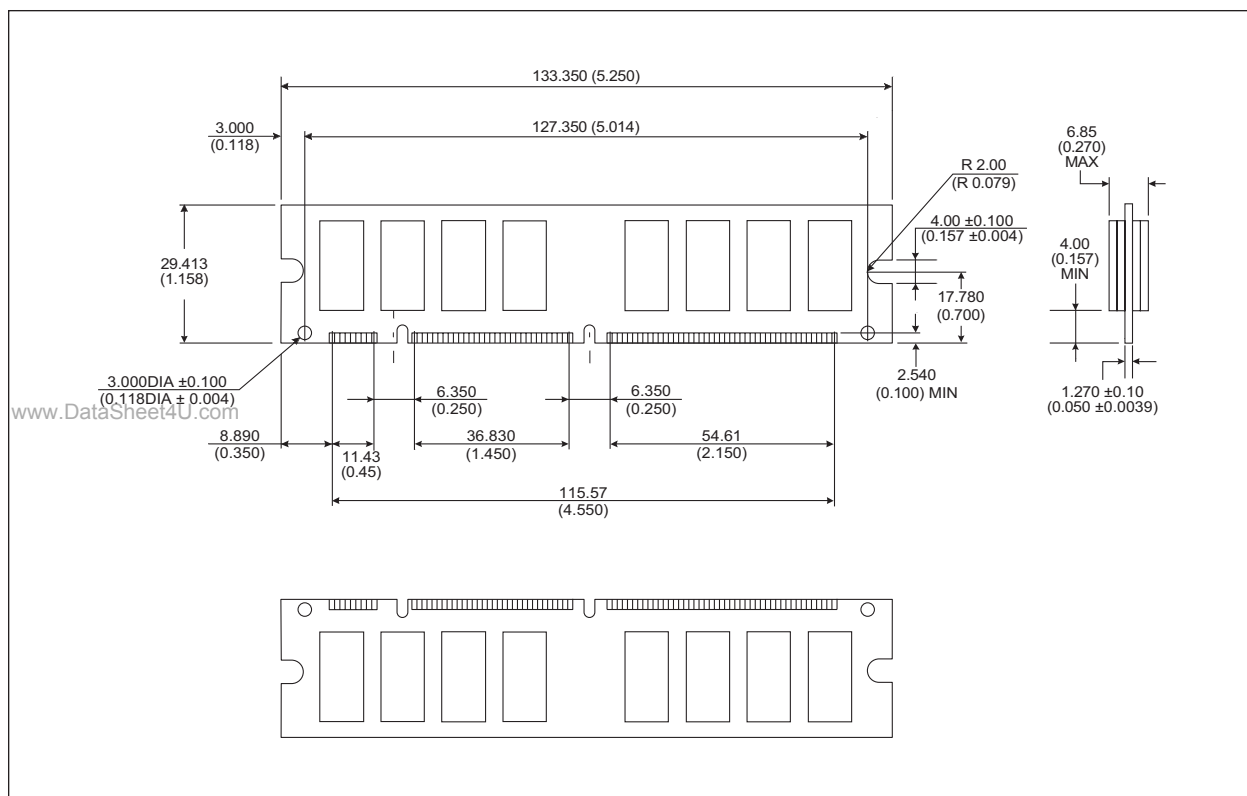
ORDERING INFORMATION

Part Number	Speed	CAS Latency	Height*
WV3DG64127V10D2	100MHz	CL=2	29.41 (1.158")
WV3DG64127V7D2	133MHz	CL=2	29.41 (1.158")
WV3DG64127V75D2	133MHz	CL=3	29.41 (1.158")

NOTES:

- Consult Factory for availability of Lead-Free products. (F = Lead-Free, G = RoHS Compliant)
- Vendor specific part numbers are used to provide memory components source control. The place holder for this is shown as lower case "x" in the part numbers above and is to be replaced with the respective vendors code. Consult factory for qualified sourcing options. (M = Micron, S = Samsung & consult factory for others)
- Consult factory for availability of industrial temperature (-40°C to 85°C) option

PACKAGE DIMENSIONS



*ALL DIMENSIONS ARE IN MILLIMETERS AND (INCHES)



Document Title

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Revision History

Rev #	History	Release Date	Status
Rev 0	Created	4-05	Advanced

www.DataSheet4U.com